H-BRIDGE-MOS

60V HBRIDGE-DRIVE-2NP-Channel Advanced Power MOSFET

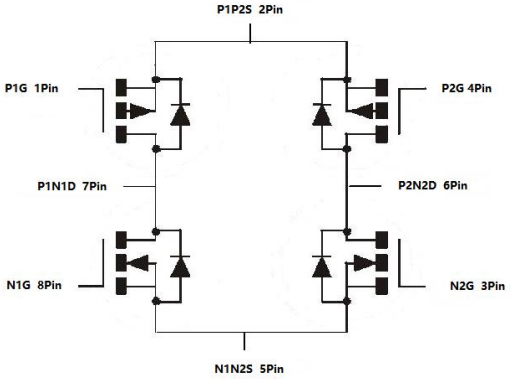
Summary

Device	$V_{(BR)DSS}$	Q_G	$R_{DS(on)}$
N-CH	60V	9.0nC	25mΩ @ V_{GS}= 10V
			45mΩ @ V_{GS}= 4.5V
P-CH	-60V	12.7nC	50mΩ @ V_{GS}= -10V
			75mΩ @ V_{GS}= -4.5V

Description

This new generation complementary MOSFET H-Bridge

features low on-resistance achievable with low gate drive.

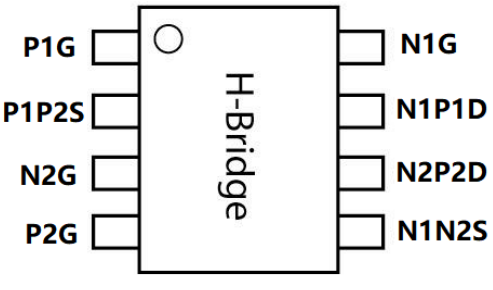


Features

- 2 x N + 2 x P channels in a SOIC package
- Low voltage (V_{GS} = 4.5 V) gate drive

Applications

- DC Motor control
- DC-AC Inverters



Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
5HB06N8	13	12	2,500

Device marking

WFS
5HB06N8

Absolute maximum ratings

Parameter	Symbol	N-channel	P-channel	Unit
Drain-Source voltage	V_{DSS}	60	-60	V
Gate-Source voltage	V_{GS}	±20	±20	V
Continuous Drain current @ V_{GS}= 10V; T_A=25°C (b)	I_D	4.98	-4.13	A
@ V_{GS}= 10V; T_A=70°C (b)		3.98	-3.31	
@ V_{GS}= 10V; T_A=25°C (a)		3.98	-3.36	
@ V_{GS}= 10V; T_L=25°C (f)		4.17	-3.51	
Pulsed Drain current @ V_{GS}= 10V; T_A=25°C (c)	I_{DM}	22.9	-19.6	A
Continuous Source current (Body diode) at T_A =25°C (b)	I_S	2.0	-2.0	A
Pulsed Source current (Body diode) at T_A =25°C (c)	I_{SM}	22.9	-19.6	A
Power dissipation at T_A =25°C (a)	PD	0.87		W
Linear derating factor		6.94		mW/°C
Power dissipation at T_A =25°C (b)	PD	1.35		W
Linear derating factor		10.9		mW/°C
Power dissipation at T_L =25°C (f)	PD	0.95	0.98	W
Linear derating factor		7.63	7.81	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150		°C

Thermal resistance

Parameter	Symbol	Value		Unit
Junction to ambient (a)	$R_{\theta JA}$	144		°C/W
Junction to ambient (b)	$R_{\theta JA}$	92		°C/W
Junction to ambient (d)	$R_{\theta JA}$	106		°C/W
Junction to ambient (e)	$R_{\theta JA}$	254		°C/W
Junction to lead (f)	$R_{\theta JL}$	131	128	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions with the heat-sink split into two equal areas (one for each drain connection); the device is measured when operating in a steady-state condition with one active die.

(b) Same as note (a), except the device is measured at t ≤ 10 sec.

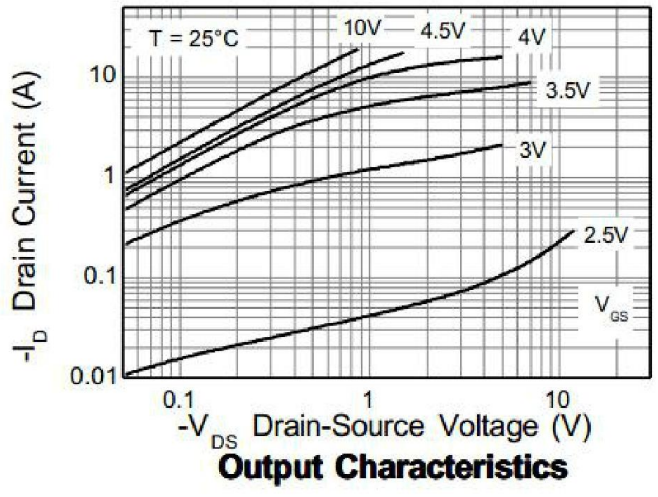
(c) Same as note (a), except the device is pulsed with D= 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.

(d) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions with the heat-sink split into two equal areas (one for each drain connection); the device is measured when operating in a steady-state condition with one active die.

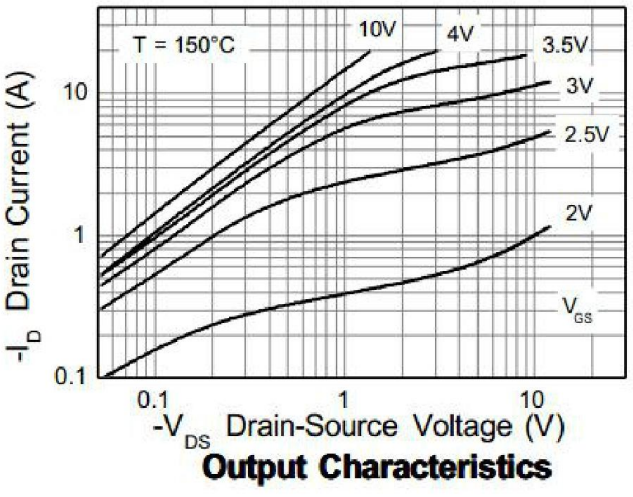
(e) For a device surface mounted on minimum copper 1.6mm FR4 PCB, in still air conditions; the device is measured when operating in a steady-state condition with one active die.

(f) Thermal resistance from junction to solder-point (at the end of the drain lead); the device is operating in a steady-state condition with one active die.

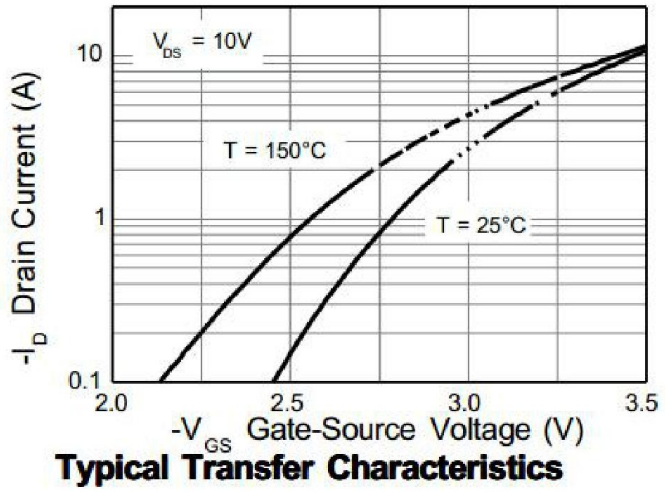
N-channel typical characteristics



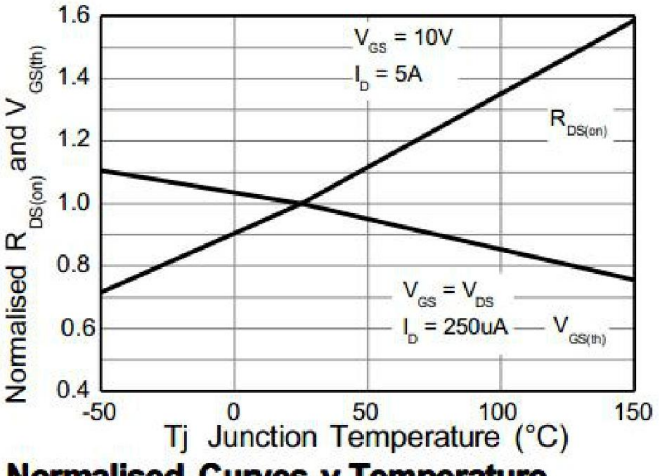
Output Characteristics



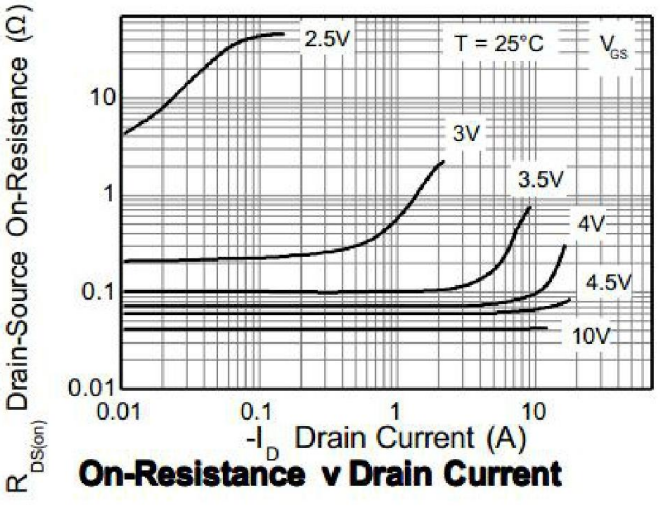
Output Characteristics



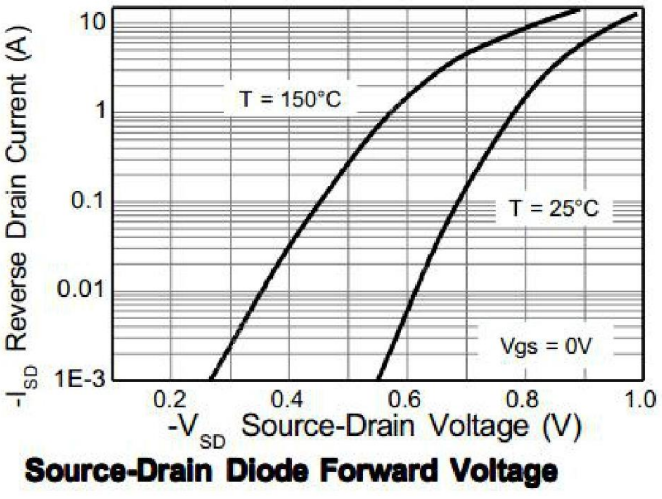
Typical Transfer Characteristics



Normalised Curves v Temperature

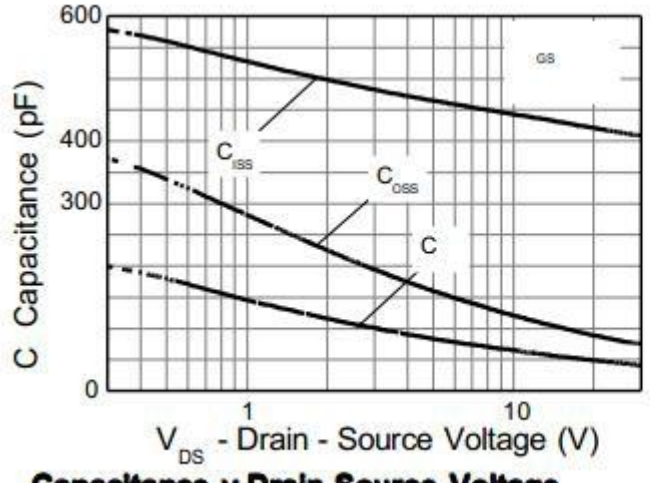


On-Resistance v Drain Current

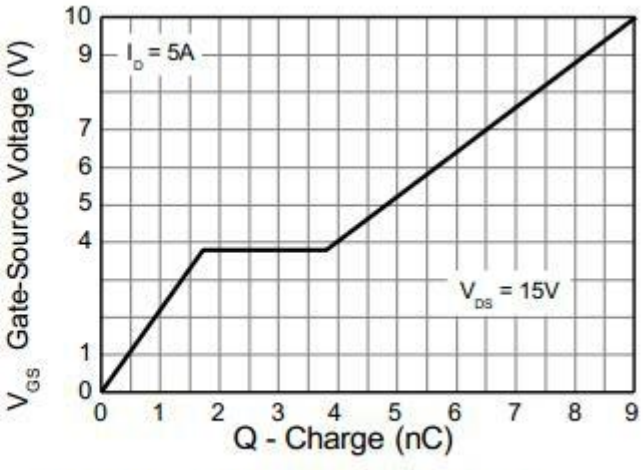


Source-Drain Diode Forward Voltage

N-channel typical characteristics -continued

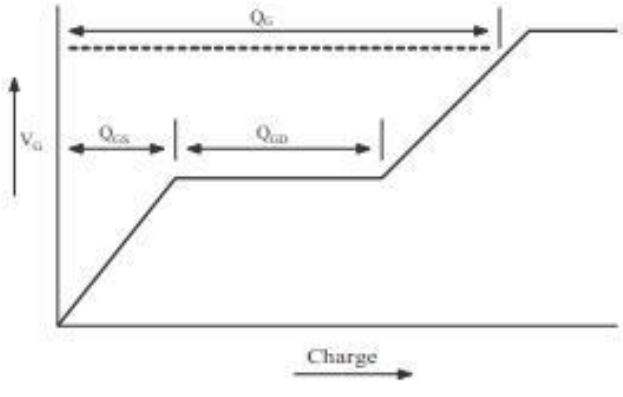


Capacitance v Drain-Source Voltage

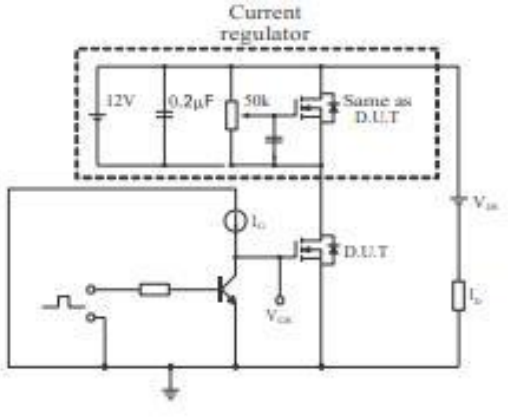


Gate-Source Voltage v Gate Charge

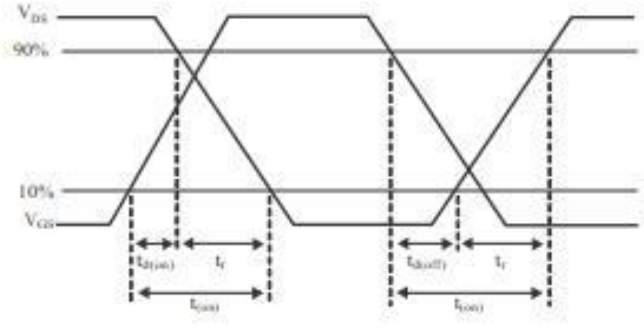
Test circuits



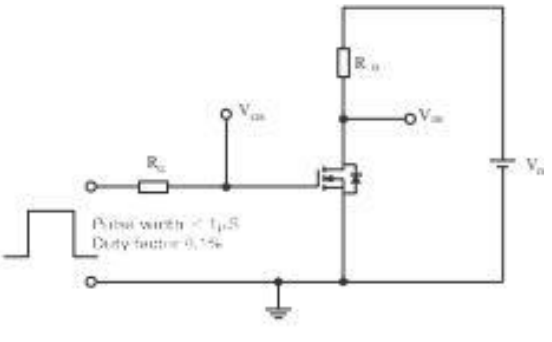
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

N-channel electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	60			V	ID = 250μA, VGS= 0V
Zero Gate voltage Drain current	I_{DSS}			0.5	μA	VDS= 30V, VGS= 0V
Gate-Body leakage	I_{GSS}			±100	nA	V_{GS} = ±20V, V_{DS} = 0V
Gate-Source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	ID= 250μA, VDS= VGS
Static Drain-Source on-state resistance (a)	$R_{DS(on)}$			0.025 0.045	Ω	VGS= 10V, ID= 5A VGS= 4.5V, ID= 4A
Forward Transconductance (a) (c)	g_{fs}		11.8		S	VDS= 15V, ID= 5A
Dynamic						
Capacitance (c)						
Input capacitance	C_{iss}		430		pF	VDS= 15V, VGS= 0V f= 1MHz
Output capacitance	C_{oss}		101		pF	
Reverse transfer capacitance	C_{rss}		56		pF	
Switching (b) (c)						
Turn-on-delay time	$t_{d(on)}$		2.5		ns	VDD= 15V, VGS= 10V ID= 1A RG ≅ 6Ω,
Rise time	tr		3.3		ns	
Turn-off delay time	$t_{d(off)}$		11.5		ns	
Fall time	tf		6.3		ns	
Gate charge (c)						
Total Gate charge	Qg		9.0		nC	VDS=15V, VGS= 10V ID= 5A
Gate-Source charge	Q_{gs}		1.7		nC	
Gate-Drain charge	Q_{gd}		2.0		nC	
Source–Drain diode						
Diode forward voltage (a)	V_{SD}		0.82	1.2	V	IS= 1.7A, VGS= 0V
Reverse recovery time (c)	t_{rr}		12		ns	IS= 2.1A, di/dt= 100A/μs
Reverse recovery charge (c)	Q_{rr}		4.9		nC	

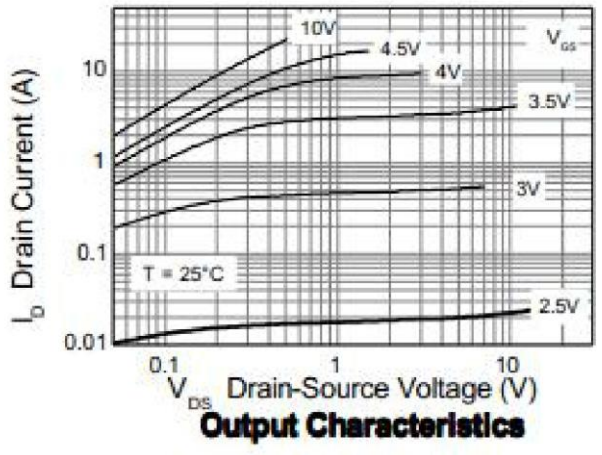
NOTES:

(a) Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.

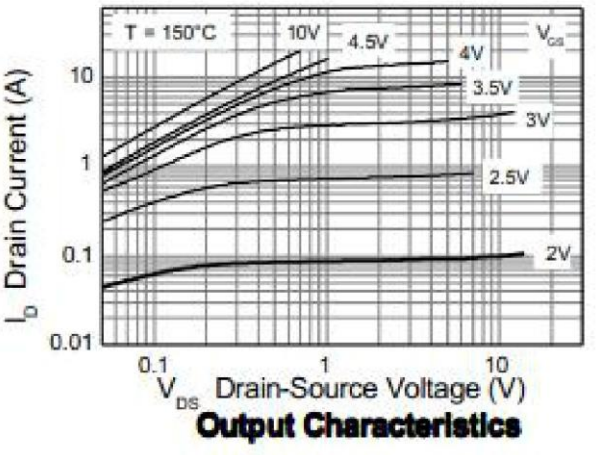
(b) Switching characteristics are independent of operating junction temperature.

For design aid only, not subject to production testing

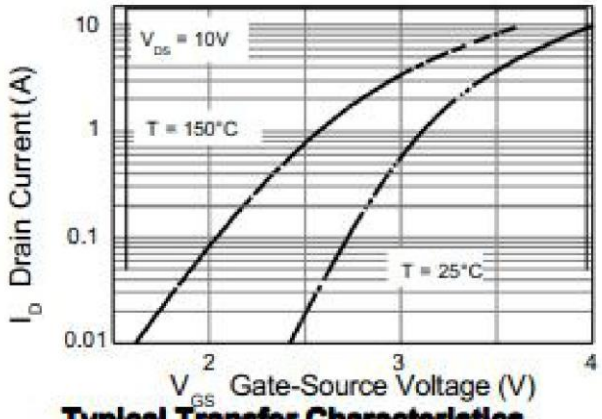
N-channel typical characteristics



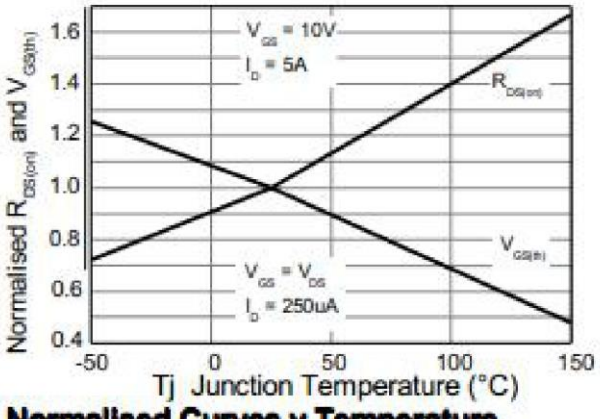
Output Characteristics



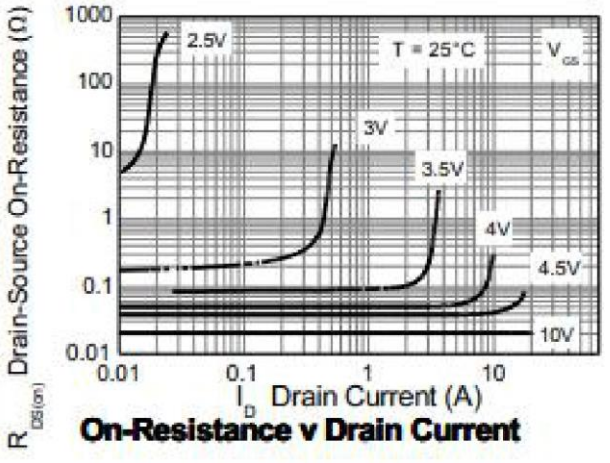
Output Characteristics



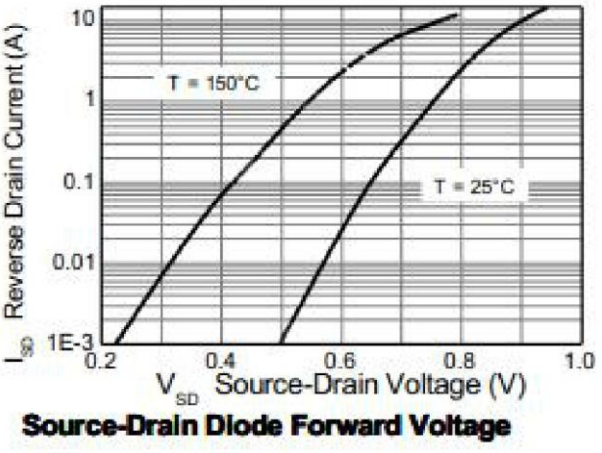
Typical Transfer Characteristics



Normalised Curves v Temperature



On-Resistance v Drain Current



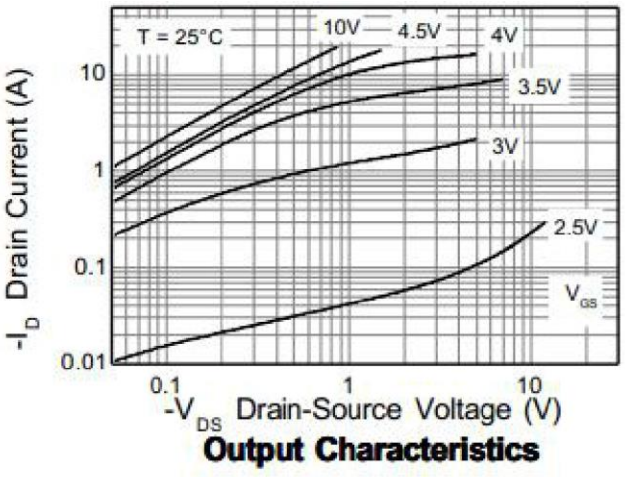
Source-Drain Diode Forward Voltage

maspower

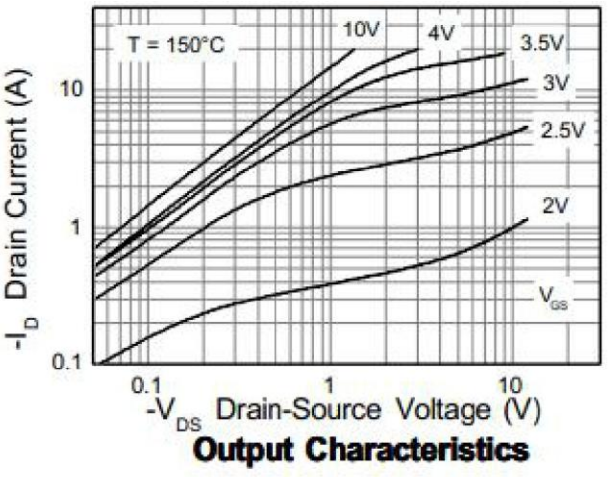
P-channel electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	-60			V	ID = 250µA, VGS= 0V
Zero Gate voltage Drain current	I_{DSS}			0.5	µA	VDS= 30V, VGS= 0V
Gate-Body leakage	I_{GSS}			±100	nA	V_{GS} = ±20V, V_{DS} = 0V
Gate-Source threshold voltage	$V_{GS(th)}$	1.0		3.0	V	ID= 250µA, VDS= VGS
Static Drain-Source on-state resistance (a)	$R_{DS(on)}$			0.050 0.075	Ω	VGS= -10V, ID= -5A VGS= -4.5V, ID= -4A
Forward Transconductance (a) (c)	g_{fs}		14		S	VDS= -15V, ID= -5A
Dynamic						
Capacitance (c)						
Input capacitance	C_{iss}		670		pF	VDS= -15V, VGS=0V f= 1MHz
Output capacitance	C_{oss}		126		pF	
Reverse transfer capacitance	C_{rss}		70		pF	
Switching (b) (c)						
Turn-on-delay time	$t_{d(on)}$		1.9		ns	VDD= -15V, VGS= -10V ID= -1A RG ≅ 6Ω,
Rise time	tr		3.0		ns	
Turn-off delay time	$t_{d(off)}$		30		ns	
Fall time	tf		21		ns	
Gate charge (c)						
Total Gate charge	Qg		12.7		nC	VDS=-15V, VGS= -10V ID= -5A
Gate-Source charge	Q_{gs}		2.0		nC	
Gate-Drain charge	Q_{gd}		2.4		nC	
Source–Drain diode						
Diode forward voltage (a)	V_{SD}		-0.82	-1.2	V	IS= -1.7A, VGS= 0V
Reverse recovery time (c)	t_{rr}		16.5		ns	IS= -2.1A, di/dt= 100A/µs
Reverse recovery charge (c)	Q_{rr}		11.5		nC	

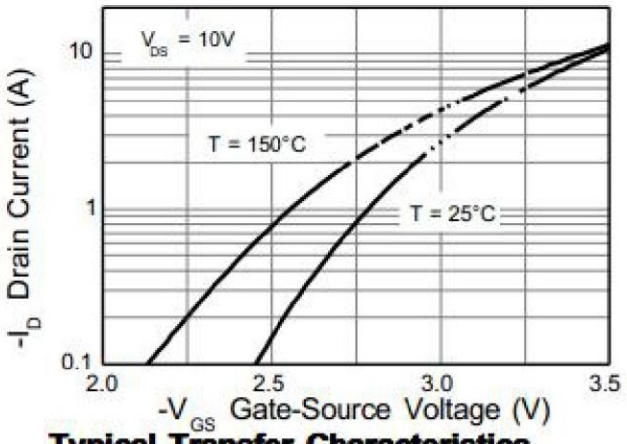
P-channel typical characteristics



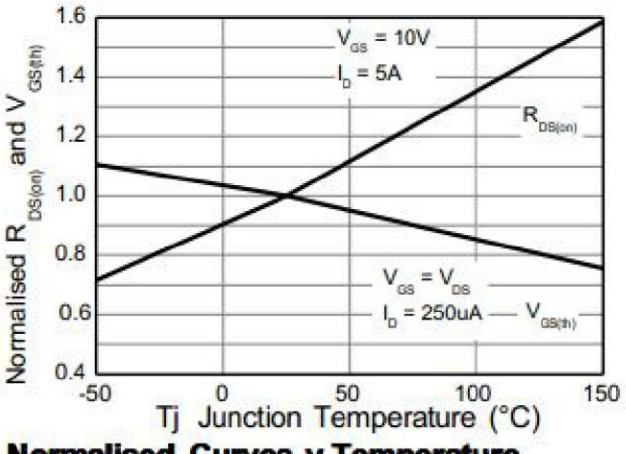
Output Characteristics



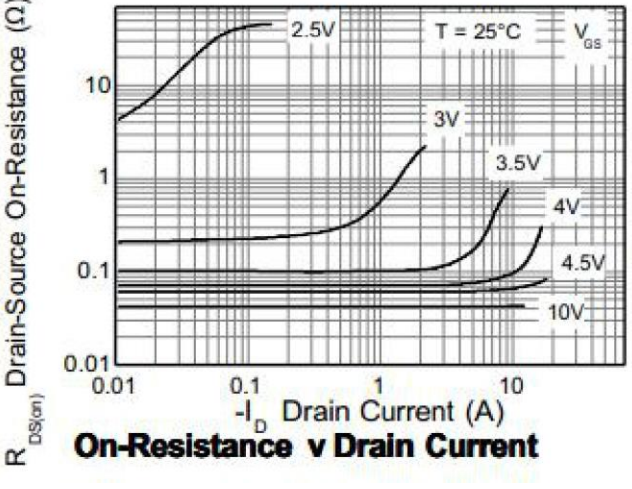
Output Characteristics



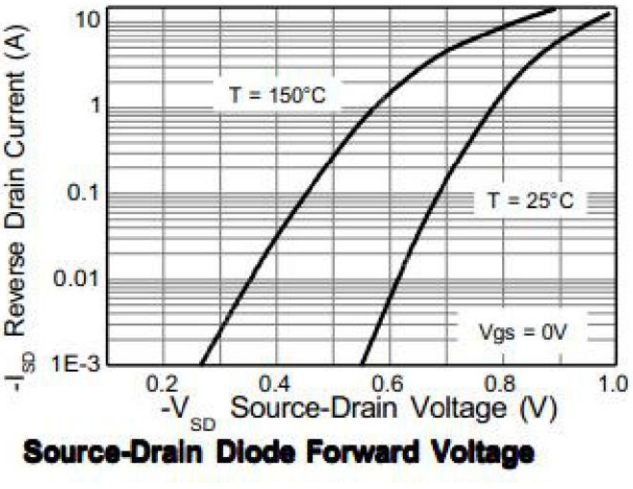
Typical Transfer Characteristics



Normalised Curves v Temperature

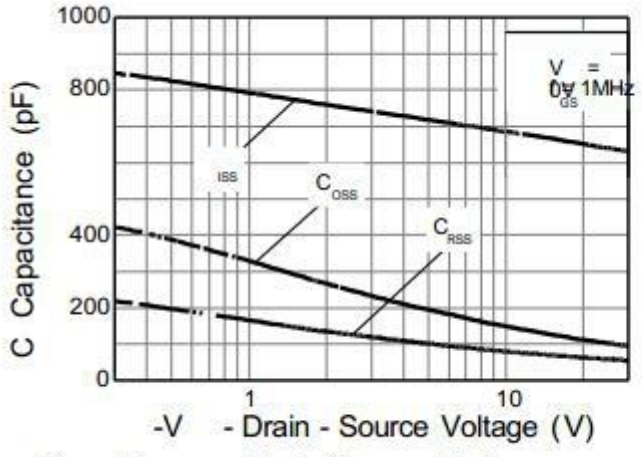


On-Resistance v Drain Current

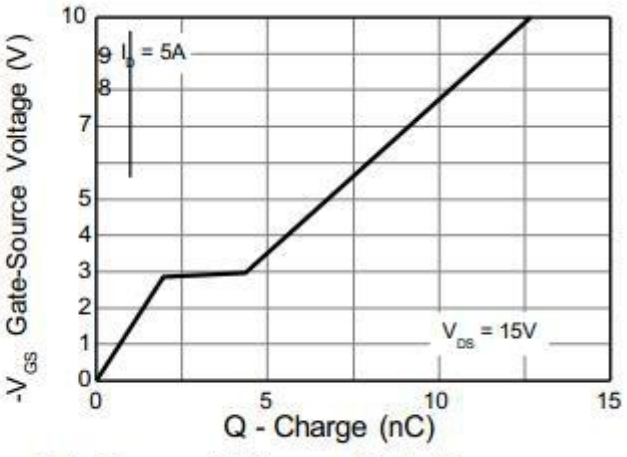


Source-Drain Diode Forward Voltage

P-channel typical characteristics -continued

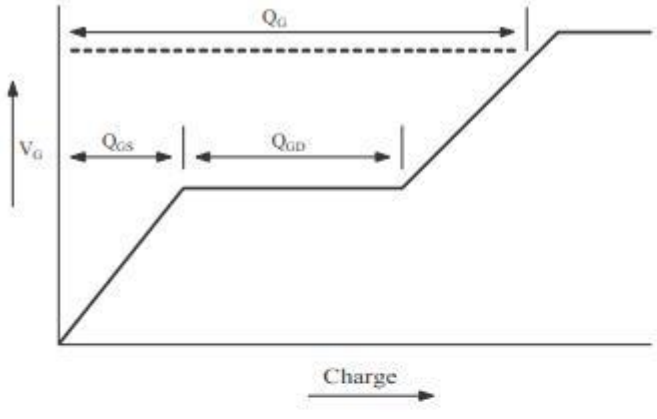


Capacitance v Drain-Source Voltage

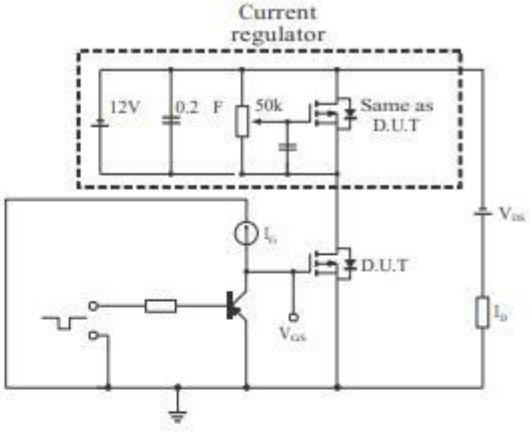


Gate-Source Voltage v Gate Charge

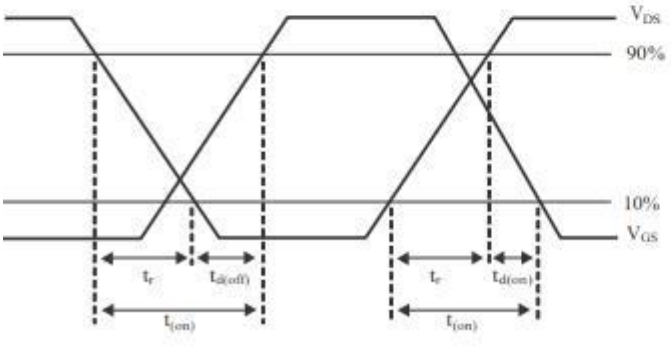
Test circuits



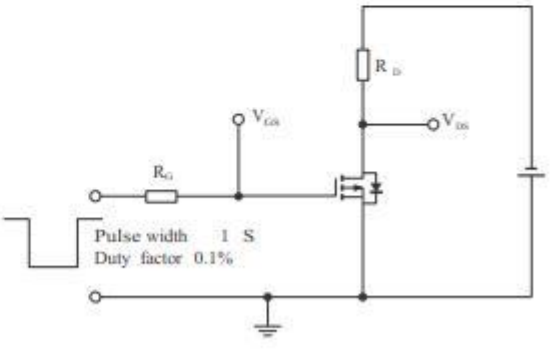
Basic gate charge waveform



Gate charge test circuit

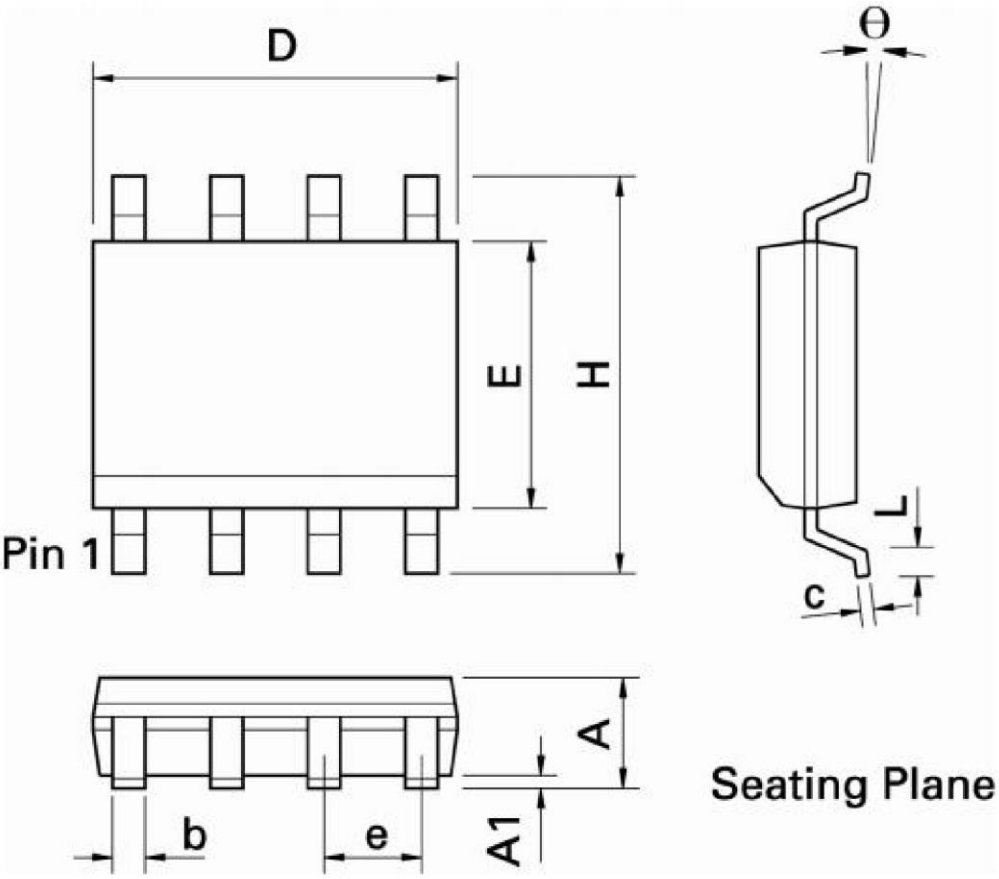


Switching time waveforms



Switching time test circuit

Packaging details -SO8



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	-	-	-	-	-
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters